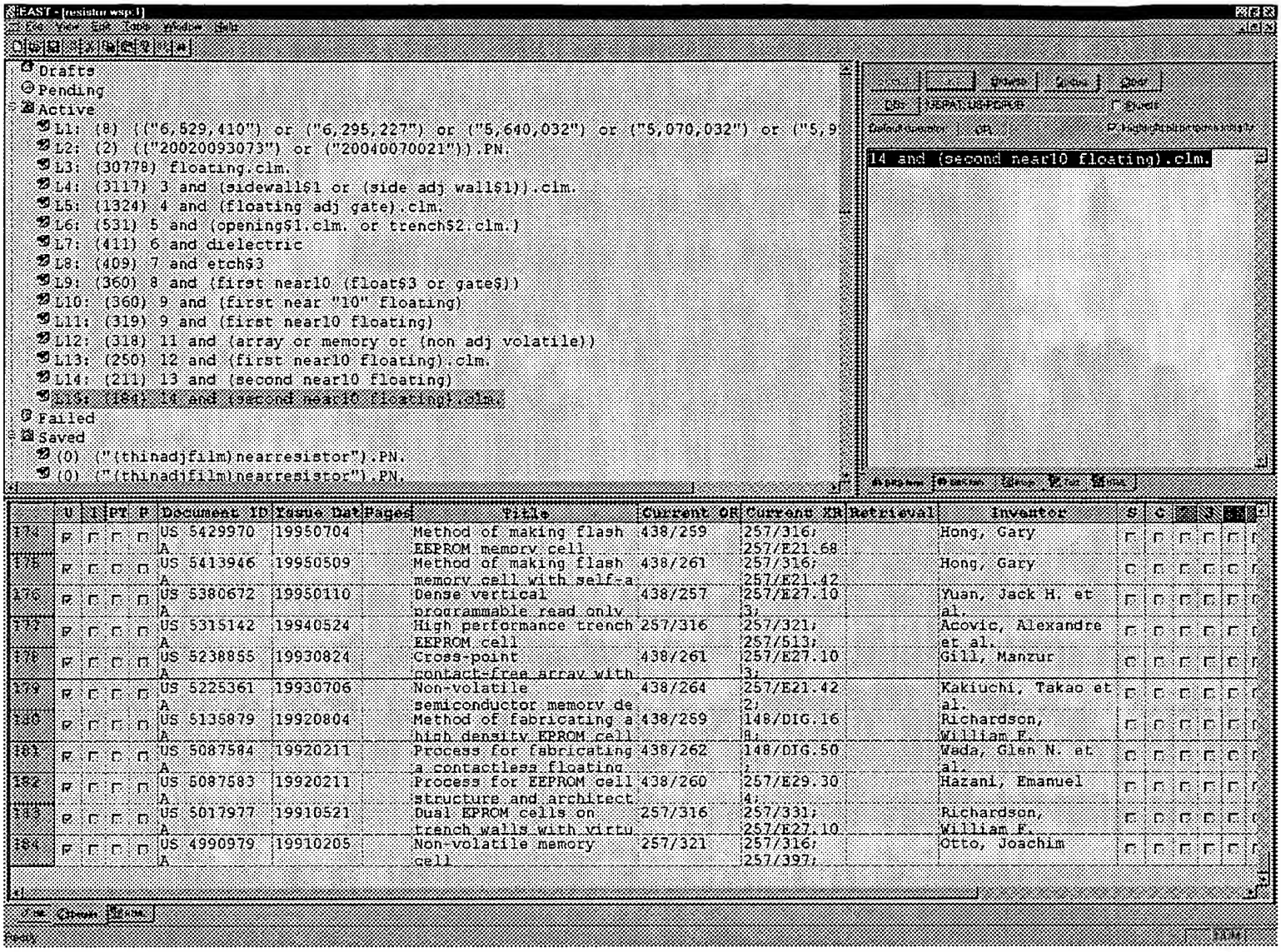

	U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C
174	P				US 5429970 A	19950704		Method of making flash EEPROM memory cell	438/259	257/316; 257/E21.68		Hong, Gary		
175	P				US 5413946 A	19950509		Method of making flash memory cell with self-a	438/261	257/316; 257/E21.42		Hong, Gary		
176	P				US 5380672 A	19950110		Dense vertical programmable read only	438/257	257/E27.10 3;		Yuan, Jack H. et al.		
177	P				US 5315142 A	19940524		High performance trench EEPROM cell	257/316	257/321; 257/513;		Acovic, Alexandre et al.		
178	P				US 5238855 A	19930824		Cross-point contact-free array with	438/261	257/E27.10 3;		Gill, Manzur		
179	P				US 5225361 A	19930706		Non-volatile semiconductor memory de	438/264	257/E21.42 2;		Kakiuchi, Takao et al.		
180	P				US 5135879 A	19920804		Method of fabricating a high density EPROM cell	438/259	148/DIG.16 8;		Richardson, William F.		
181	P				US 5087584 A	19920211		Process for fabricating a contactless floating	438/262	148/DIG.50 ;		Wada, Glen N. et al.		
182	P				US 5087583 A	19920211		Process for EEPROM cell structure and architect	438/260	257/E29.30 4;		Hazani, Emanuel		
183	P				US 5017977 A	19910521		Dual EPROM cells on trench walls with virtu	257/316	257/331; 257/E27.10		Richardson, William F.		
184	P				US 4990979 A	19910205		Non-volatile memory cell	257/321	257/316; 257/397;		Otto, Joachim		